Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Low collector-emitter saturation voltage VCEsat
- High collector current capability IC and ICM
- · High collector current gain (hFE) at high IC
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- DC-to-DC conversion
- · MOSFET gate driving
- · Motor control
- · Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	20	V
I _C	collector current		-	-	5.8	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	11.6	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	30	43	mΩ

5. Pinning information

Table 2. Pinning information

Table 2.1 milling information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	В	base	4	С			
2	С	collector					
3	Е	emitter		B—[
4	С	collector	□1 □2 □3	Ė			
			SC-73 (SOT223)	sym123			



20 V, 5.8 A NPN low VCEsat transistor

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS302NZ-Q		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS302NZ-Q	S302NZ

8. Limiting values

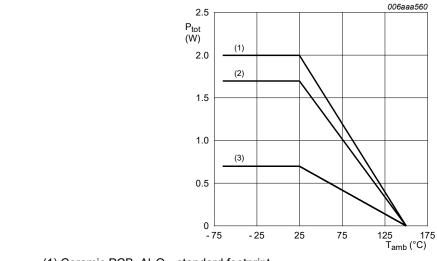
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	20	V
V_{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	5.8	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	11.6	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.7	W
			[2]	-	1.7	W
			[3]	-	2	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

20 V, 5.8 A NPN low VCEsat transistor



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	179	K/W
	junction to ambient		[2]	-	-	74	K/W
			[3]	-	-	63	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

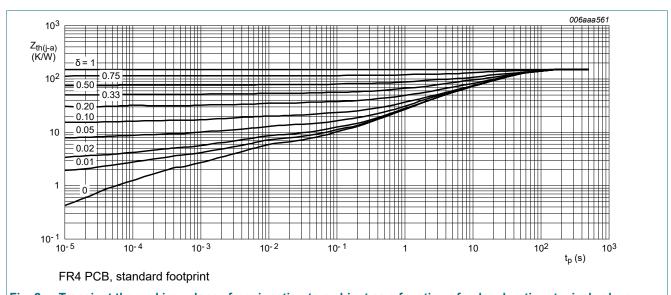


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, 5.8 A NPN low VCEsat transistor

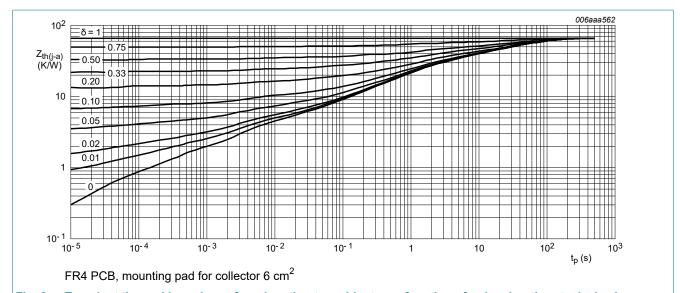


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

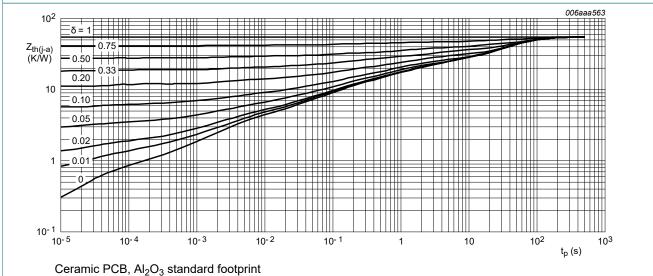


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, 5.8 A NPN low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 20 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	570	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	550	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	250	520	-	
		V_{CE} = 2 V; I_{C} = 4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	450	-	
		V_{CE} = 2 V; I_{C} = 7 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	200	350	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 0.5 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	20	25	mV
		I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	35	50	mV
		I_C = 1 A; I_B = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	50	70	mV
		I_C = 2 A; I_B = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	70	100	mV
		I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	120	170	mV
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	115	165	mV
		I_C = 4 A; I_B = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	155	240	mV
		I_C = 5.8 A; I_B = 290 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	170	250	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	30	43	mΩ
		I_C = 4 A; I_B = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	38	60	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.82	0.9	V
		$I_C = 4 \text{ A}; I_B = 400 \text{ mA}; \text{ pulsed}; t_p \le 300 \text{ µs}; \delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	-	0.92	1.05	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.75	0.85	V
·d	delay time	V _{CC} = 12.5 V; I _C = 3 A; I _{Bon} = 0.15 A;	-	15	-	ns
·r	rise time	I _{Boff} = -0.15 A; T _{amb} = 25 °C	-	40	-	ns
on	turn-on time		-	55	-	ns
·S	storage time	1	-	270	-	ns
t _f	fall time		-	85	-	ns
off	turn-off time	1	-	335	-	ns

20 V, 5.8 A NPN low VCEsat transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	140	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	95	150	pF

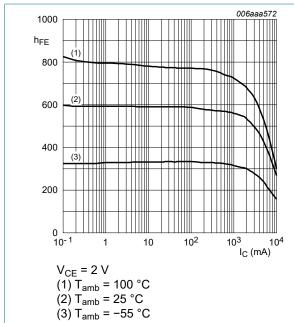


Fig. 5. DC current gain as a function of collector current; typical values

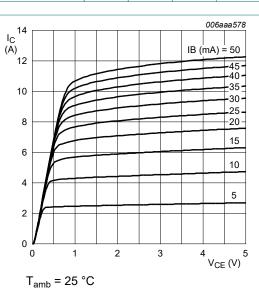
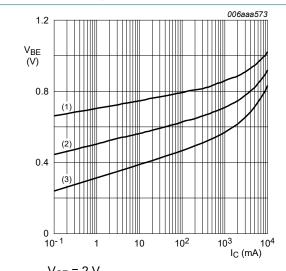
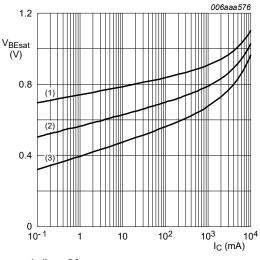


Fig. 6. Collector current as a function of collectoremitter voltage; typical values





(3) T_{amb} = 100 °C Fig. 7. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) $T_{\rm amb} = -55~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = 100~{\rm ^{\circ}C}$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

20 V, 5.8 A NPN low VCEsat transistor

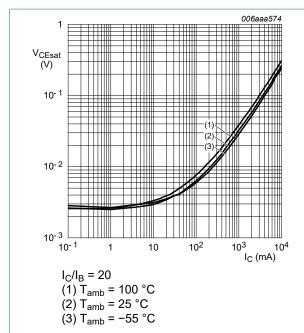


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

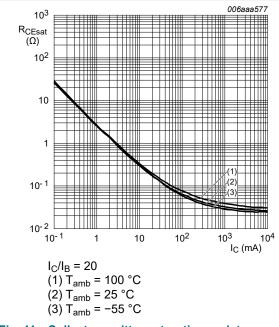


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

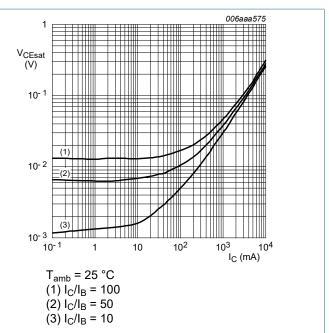


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

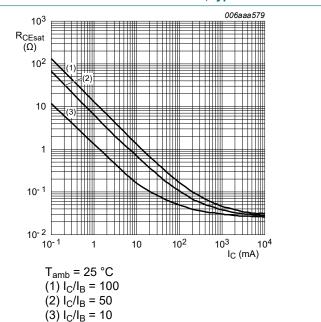
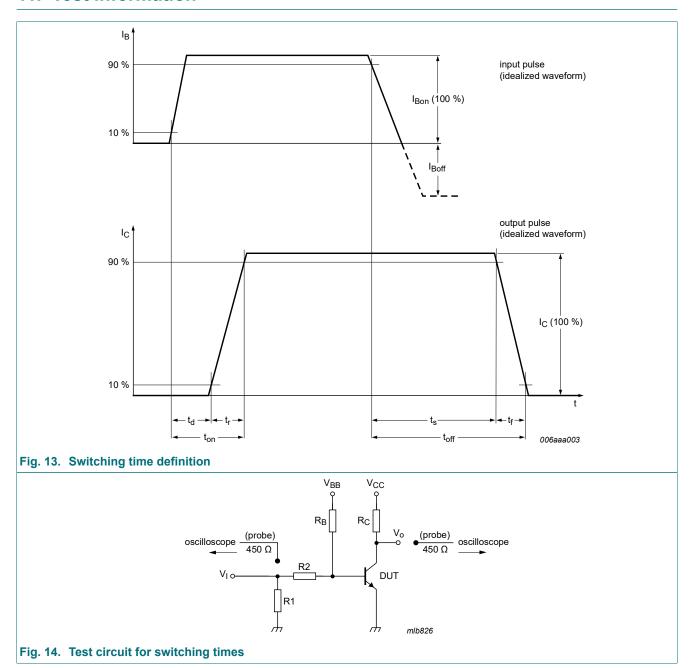


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

20 V, 5.8 A NPN low VCEsat transistor

11. Test information

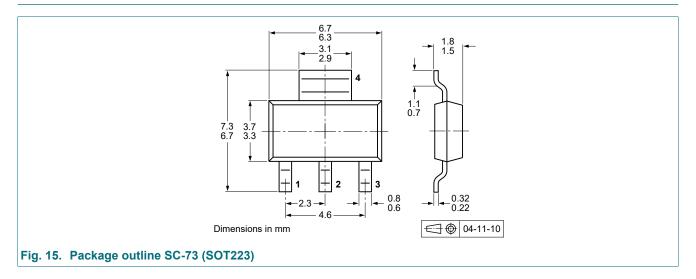


Quality information

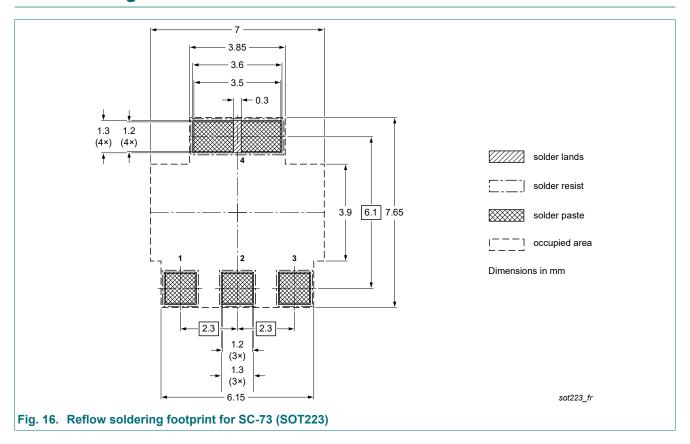
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

20 V, 5.8 A NPN low VCEsat transistor

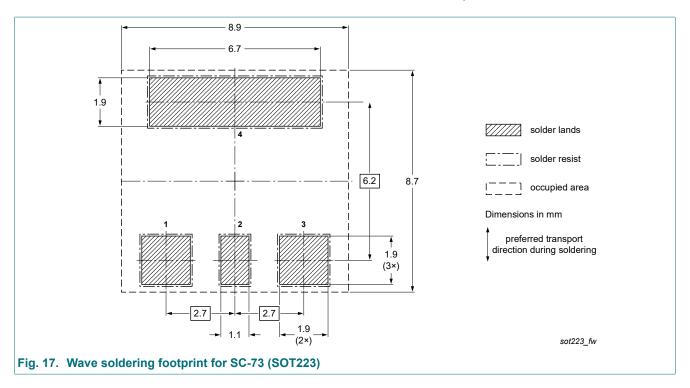
12. Package outline



13. Soldering



20 V, 5.8 A NPN low VCEsat transistor



20 V, 5.8 A NPN low VCEsat transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS302NZ-Q v.1	20230112	Product data sheet	-	-

20 V, 5.8 A NPN low VCEsat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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20 V, 5.8 A NPN low VCEsat transistor

Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	1
6. Ordering information	2
7. Marking	2
8. Limiting values	2
9. Thermal characteristics	3
10. Characteristics	5
11. Test information	8
12. Package outline	9
13. Soldering	9
14. Revision history	
15. Legal information	

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13 / 13

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